

Electrical characterization of p- and n- type 150um epi-Si diodes irradiated by protons and neutrons

Monday 2 June 2008 13:30 (20 minutes)

Epi-Si 150 um thick diodes on p- and n-type bulk were studied after irradiation by 24 GeV/c protons (CERN PS) and reactor neutrons (Ljubljana) up to equivalent fluence of several times $10^{15}/\text{cm}^2$ and following isothermal annealing at 80°C.

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Session Classification: Defect Engineering & Pad Detector Characterization I

Track Classification: Defect Engineering and Pad Detector Characterization